

isc N-Channel MOSFET Transistor

IRF236

DESCRIPTION

- Drain Current $I_D=8.1A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 275V(Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)}=0.45\ \Omega (Max)$
- Nanosecond Switching speeds

APPLICATIONS

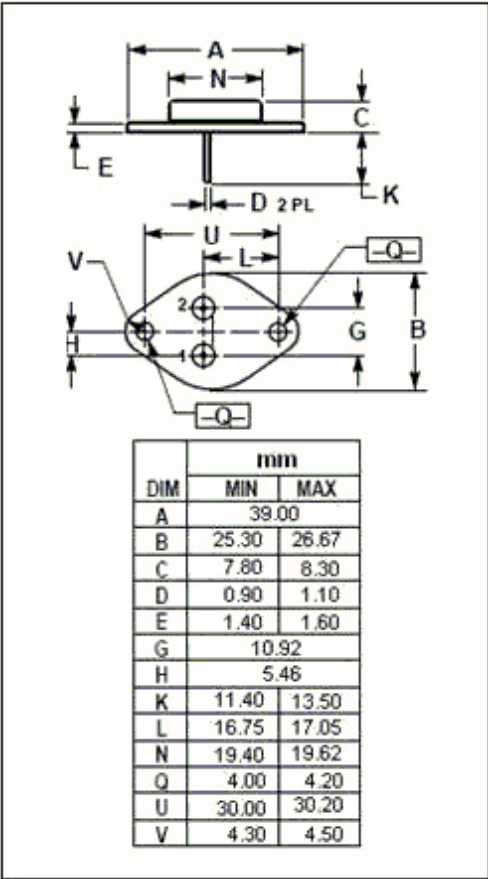
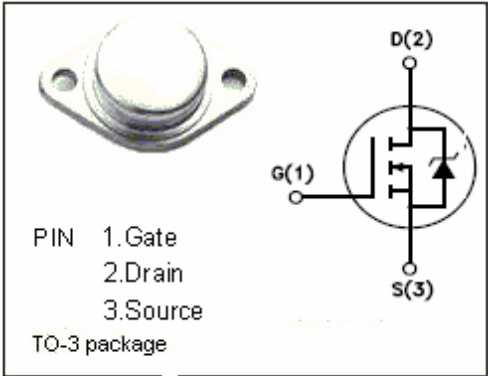
- Switching power supplies
- Switching converters,motor driver,relay driver
- Drivers for high-power bipolar switching transistors

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	275	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^{\circ}C$	8.1	A
P_{tot}	Total Dissipation@ $T_C=25^{\circ}C$	75	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.67	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	80	$^{\circ}C/W$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=250\mu\text{A}$	275			V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=250\mu\text{A}$	2.0		4.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}$; $I_D=4.1\text{A}$			0.45	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=275\text{V}$; $V_{GS}=0$			250	μA
V_{SD}	Diode Forward Voltage	$I_S=8.1\text{A}$; $V_{GS}=0$			2.0	V
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}$; $V_{GS}=0\text{V}$; $f_T=1\text{MHz}$		600		pF
C_{rss}	Reverse Transfer Capacitance			52		
C_{oss}	Output Capacitance			180		
t_r	Rise Time	$R_{GS}=15\Omega$ $I_D=5\text{A}$; $V_{DD}=90\text{V}$; $R_L=15\Omega$		23	35	ns
$t_{d(on)}$	Turn-on Delay Time			9.1	14	
t_f	Fall Time			19	29	
$t_{d(off)}$	Turn-off Delay Time			31	47	